

## **AMENDMENTS TO THE SPECIFICATION:**

Please replace the paragraph beginning on page 7, line 8 with the following replacement paragraph:

--It is also optionally possible for the oblique surfaces to be formed as a multiplicity of pyramids or as pyramid-shaped depressions in subsections 4a. These may be spaced at regular intervals or, however, also randomly distributed. This pyramid structure may be produced, just as the V-shaped grooves discussed above, by deeply etching the silicon substrate, for which, then, suitably modified etching masks are needed. For further details on a specific embodiment of this kind of material measuring standard according to the present invention, reference is additionally made here, for example, to the publication by I. Zubel, Silicon Anisotropic Etching in Alkaline Solutions II, Sensors and Actuators, A 70 (1998), pp. 260 - 268, ~~which is incorporated herein by reference.--~~.